

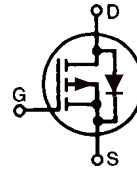
Standard Power MOSFET

IXTH 16P20

$$\begin{aligned} V_{DSS} &= -200 \text{ V} \\ I_{D25} &= -16 \text{ A} \\ R_{DS(on)} &= 0.16 \Omega \end{aligned}$$

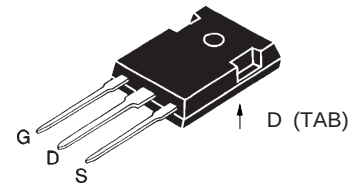
P-Channel Enhancement Mode
Avalanche Rated

Preliminary Data Sheet



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	-200	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	-200	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	-16	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_J	-64	A
I_{AR}	$T_C = 25^\circ\text{C}$	-16	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-247 AD



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard package JEDEC TO-247 AD
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance (<5 nH)
- easy to drive and to protect

Applications

- High side switching
- Push-pull amplifiers
- DC choppers
- Automatic test equipment

Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- Space savings
- High power density

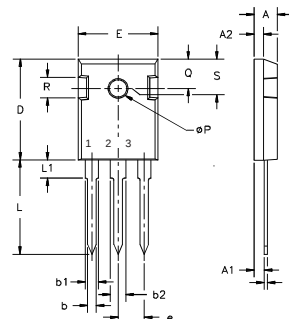
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = -250 \mu\text{A}$	-200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-3.0		-5.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$			-25 μA
	$V_{GS} = 0 \text{ V}$			-1 mA
$R_{DS(on)}$	$V_{GS} = -10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$			0.16 Ω

Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	V _{DS} = -10 V; I _D = I _{D25} , pulse test	6	10	S
C_{iss}	} V _{GS} = 0 V, V _{DS} = -25 V, f = 1 MHz	2800		pF
C_{oss}		550		pF
C_{rss}		240		pF
t_{d(on)}	} V _{GS} = -10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25} R _G = 4.7 Ω (External)	33		ns
t_r		26		ns
t_{d(off)}		65		ns
t_f		25		ns
Q_{g(on)}	} V _{GS} = -10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}	95		nC
Q_{gs}		27		nC
Q_{gd}		40		nC
R_{thJC}			0.42	K/W
R_{thCS}		0.25		K/W

Source-Drain Diode

Source-Drain Diode		Characteristic Values (T _J = 25°C, unless otherwise specified)	
Symbol	Test Conditions	min.	typ. max.
I _S	V _{GS} = 0		-16 A
I _{SM}	Repetitive; pulse width limited by T _{JM}		-64 A
V _{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %		-3 V
t _{rr}	I _F = I _S , di/dt = 100 A/μs, V _R = -50 V	250	ns

TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain
 3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC



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